

Radiation induced oscillations of the Hall resistivity in two-dimensional electron systems

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We consider the effect of microwave radiation on the Hall resistivity in two-dimension electron systems. It is shown that photon-assisted impurity scattering of electrons can result in oscillatory dependences of both dissipative and Hall components of the conductivity and resistivity tensors on the ratio of radiation frequency to cyclotron frequency. The Hall resistivity can include a component induced by microwave radiation which is an even function of the magnetic field. The phase of the dissipative resistivity oscillations and the polarization dependence of their amplitude are compared with those of the Hall resistivity oscillations. The developed model can clarify the results of recent experimental observations of the radiation induced Hall effect.

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The oscillatory dependence of the conductivity of two-dimensional electron systems (2DES's) under microwave radiation in a magnetic field on the ratio of radiation frequency Ω to cyclotron frequency Ω_c has been predicted more than three decades ago by the author [1] (see also Ref. [2]). As shown [1, 2], the variation of the dissipative conductivity caused by irradiation (microwave photoconductivity) is negative if Ω somewhat exceeds $\Lambda\Omega_c$, where $\Lambda = 1, 2, 3, \dots$. In this situation, the net dissipative conductivity can become negative if the incident microwave power is sufficiently high (effect of absolute negative conductivity or ANC). The oscillations of the dissipative components of the conductivity tensor σ_{xx} and σ_{yy} considered in Refs. [1, 2] are associated with photon-assisted impurity scattering of electrons accompanied by their transitions between the Landau levels (LL's). As shown in Refs. [3, 4, 5, 6], photon-assisted impurity scattering can result in variations of the Hall conductivity components σ_{xy} and σ_{yx} (with $\sigma_{xy} \neq -\sigma_{yx}$ due to an even dependence of such variations on the magnetic field). The oscillatory dependences of the dissipative conductivity in a 2DES as a function of Ω/Ω_c were observed experimentally by Zudov *et al.* [7] and Ye *et al.* [8]. Shortly thereafter Mani *et al.* [9] and Zudov *et al.* [10] observed vanishing electrical resistance R_{xx} ($R_{xx} \propto \rho_{xx} = \sigma_{xx}/(\sigma_{xx}^2 + \sigma_{xy}^2)$) with increasing microwave power and formation of the so-called zero-resistance states. This effect is attributed to reaching of the threshold of ANC [5, 6, 11, 12, 13] associated with the mechanism considered in Refs. [1, 2]. The feasibility of the latter is owing to high electron mobility in the 2DES's studied, so that the cyclotron resonance and its harmonics can be observed at rather small magnetic fields and, hence, at microwave frequencies about 100 GHz and less. Since the microwave power required for ANC is approximately proportional to Ω^3 , microwave sources with moderate powers can be used at moderate magnetic fields. Further experimental results related to the oscillations of microwave photoconductivity and their consequences below and above the ANC threshold are presented in Refs. [14, 15, 16, 17, 18, 19]. In particular, Studenikin, *et*

al. [18] and Mani, *et al.* [19] demonstrated the oscillations of the Hall resistance R_{xy} which is related to the conductivity components as $R_{xy} \propto \rho_{xy} = \sigma_{xy}/(\sigma_{xx}^2 + \sigma_{xy}^2)$. One can assume that the origin of these oscillations is analogous to that discussed previously [3, 4, 5, 6].

In this paper, we calculate the dependences of ρ_{xx} and ρ_{xy} vs Ω_c/Ω using a model invoking photon-assisted impurity scattering of electrons as the main mechanism determining the microwave photoconductivity. The model under consideration generalizes that of Refs. [3, 4] in line with our recent papers [20, 21]. In principle, the concept based on photon-assisted impurity scattering as the main mechanism responsible for the observed microwave photoconductivity explains virtually all features of the effect, although it is premature to draw the final conclusions yet. Namely, the positions of the photoconductivity zeros, maxima, and minima [1, 2, 5, 6], saturation of the oscillation magnitude with increasing microwave power and, hence, relatively large magnitude of maxima and minima corresponding to the cyclotron resonance harmonics [20, 22]. A significant sensitivity of the amplitude of the microwave photoconductivity oscillations to the temperature can be attributed to the contribution of photon-assisted acoustic phonon scattering [21, 23] and an increase of the LL broadening due to increasing dependence of the electron-electron and acoustic scattering on the temperature (see, for example, Refs. [24] and [25], respectively). The experimental observation of ANC [26] associated with photon-assisted electron transitions between spatially separated states in the neighboring quantum wells (microwave hopping photoconductivity associated with similar transitions between impurity states was analyzed in Ref. [27]) is a strong argument in favor of the dynamical mechanism of ANC in 2DES's. Generally, the effect of ANC in a 2DES [28, 29] and in a 3DES [30, 31, 32] subjected to a magnetic field can also be associated with a deviation of the electron distribution function from equilibrium one. Dorozhkin [17] proposed a model based on the assumption that the electron distribution function is nonmonotonic with inversion population of the states near the center of LL's caused by the ab-

sorption of microwave radiation. In this model, the electron Larmor orbit centers hop along the dc electric field (contributing to the dissipative conductivity) both immediately absorbing microwave photons (absorption due to the photon-assisted impurity scattering) and owing to nonradiative impurity scattering upon excitation. If the maxima of the electron density of states are shifted with respect to the maxima of the distribution function, impurity scattering can, as shown by Elesin [30], lead to ANC. The main problem, however, is to realize such nontrivial electron distributions. Recently, Dmitriev, *et al.* [33] developed a similar model applied to 2DES's irradiated with microwaves in which, as assumed, the electron distribution function can be oscillatory. In this regard, the consideration of the effect of microwave radiation on the Hall conductivity is crucial to clarify genuine origin of the experimental results [7, 8, 9, 10, 14, 15, 16, 17, 18, 19].

The probability of the electron transition between the (N, k_x, k_y) and $(N', k_x + q_x, k_y + q_y)$ states in the presence of the net dc electric field $\mathbf{E} = (E, 0, 0)$ (including both the applied and Hall components) perpendicular to the magnetic field $\mathbf{H} = (0, 0, H)$ and the ac microwave field $\mathbf{E}_\Omega = (\mathcal{E}e_x, \mathcal{E}e_y, 0)$ polarized in the 2DES plane (e_x and e_y are the components of the microwave field complex polarization vector), is given by the following formula obtained on the base of the interaction representation of the operator of current via solutions of the classical equations of electron motion [3, 4, 20]:

$$W_{N, k_x, k_y; N', k_x + q_x, k_y + q_y} = \frac{2\pi\mathcal{N}_i}{\hbar} \sum_M |V_q|^2 |Q_{N, N'}(L^2 q^2/2)|^2 \times J_M^2(\xi_\Omega(q_x, q_y)) \delta[M\hbar\Omega + (N - N')\hbar\Omega_c + eEL^2 q_y]. \quad (1)$$

Here N is the LL index, k_x and k_y are the electron quantum numbers, q_x and q_y are their variations due to photon-assisted impurity scattering, $q = \sqrt{q_x^2 + q_y^2}$, $e = |e|$ is the electron charge, $\hbar$ is the Planck constant, M is the number of absorbed or emitted real

microwave photons, $\mathcal{N}_i$ is the impurity concentration, V_q is the matrix element of the electron-impurity interaction, and $Q_{N, N'}(\eta) \propto L_N^{(N' - N)}(\eta) \exp(-\eta/2)$, where $L_N^\Lambda(\eta)$ is the Laguerre polynomial. The LL form-factor is determined by the function δ characterized by the LL broadening Γ . The effect of microwave radiation is reduced to the inclusion of the energy $M\hbar\Omega$ of really absorbed or emitted M photons in the argument of the function δ in Eq. (1) and the appearance of the Bessel functions $J_M(\xi_\Omega(q_x, q_y))$ [3, 4]. Here $\xi_\Omega(q_x, q_y) = \frac{e\mathcal{E} |q_x e_x + q_y e_y - i(\Omega_c/\Omega)(q_x e_y - q_y e_x)|}{m |\Omega_c^2 - \Omega(\Omega + i\Gamma)|}$, is proportional to the amplitude of the electron orbit center oscillation in the ac microwave field (limited by the dephasing of the electron motion), where m is the electron effective mass. The quantity $\xi_\Omega(q_x, q_y)$ depends on the polarization properties of the incident radiation. At sufficiently high microwave power, the amplitude of the electron orbit center oscillation in the microwave field can become about the quantum Larmor radius L .

In the absence of microwave irradiation at moderate dc electric fields $E \ll E_c = \hbar\Omega_c/eL$, the probability of inter-LL transitions is very small. In this case, such transitions provide an exponentially small contribution to the electron dissipative conductivity [34]. At $E \lesssim E_b = \hbar\Gamma/eL$, the electron dissipative conductivity is due to electron scattering processes associated with the intra-LL transitions [35]. When a 2DES is irradiated with microwaves, the variation of the dissipative conductivity (microwave photoconductivity) can be associated with both alteration of the intra-LL scattering (that can, in particular, result in the effect of dynamic localization [26]) and appearance of the photon-assisted transitions between LL's. Considering Eq. (1), the contribution to the dissipative current Δj_D (along the axis x) associated with the photon-induced inter-LL transitions and the variation of the Hall current due to the scattering processes in question Δj_H (along the axis y) can be presented as

$$\Delta j_D = \frac{e\mathcal{N}_i}{\hbar} \sum_{M, N, N'} f_N(1 - f_{N'}) \int d^2\mathbf{q} q_y |V_q|^2 |Q_{N, N'}(L^2 q^2/2)|^2 J_M^2(\xi_\Omega(q_x, q_y)) \delta[M\hbar\Omega + (N - N')\hbar\Omega_c + eEL^2 q_y], \quad (2)$$

$$\Delta j_H = \frac{e\mathcal{N}_i}{\hbar} \sum_{M, N, N'} f_N(1 - f_{N'}) \int d^2\mathbf{q} q_x |V_q|^2 |Q_{N, N'}(L^2 q^2/2)|^2 J_M^2(\xi_\Omega(q_x, q_y)) \delta[M\hbar\Omega + (N - N')\hbar\Omega_c + eEL^2 q_y]. \quad (3)$$

Here, f_N is the filling factor of the N th Landau level given by the Fermi distribution function. Assuming for definiteness that the LL density of states is Lorentzian

with the LL-broadening $\Gamma < \Omega, \Omega_c$, at sufficiently small dc electric fields $E \ll E_b < E_c$, and ac microwave fields $\xi_\Omega(q_x, q_y) \ll 1$, for the quantities $\Delta\sigma_D = j_D/E$ and

$\Delta\sigma_H = \Delta j_H/E$ from Eqs. (2) and (3), substituting the integration over $d^2\mathbf{q}$ for the integration over $q dq d\theta$, where $\sin\theta = q_y/q$, one can obtain

$$\Delta\sigma_D \propto (1 - e^{-\hbar\Omega/T}) \int_0^{2\pi} d\theta \sin^2\theta C(\theta, \Omega, \Omega_c), \quad (4)$$

$$\Delta\sigma_H \propto (1 - e^{-\hbar\Omega/T}) \int_0^{2\pi} d\theta \sin\theta \cos\theta C(\theta, \Omega, \Omega_c), \quad (5)$$

where

$$C(P, \theta, \Omega, \Omega_c) = \mathcal{N}_i L \int dq q^2 |V_q|^2 \exp(-l^2 q^2/2) \times \sum_{M, \Lambda > 0} \frac{J_M^2(Lq\sqrt{P}f\Pi)\Theta_\Lambda \Gamma(\Lambda\Omega_c - M\Omega)}{[(\Lambda\Omega_c - M\Omega)^2 + \Gamma^2]^2}. \quad (6)$$

Here T is the temperature, $\Theta_\Lambda = \sum_N f_N(1 - f_{N+\Lambda})/\sqrt{N}$, $P \propto c\mathcal{E}^2$ is the microwave power normalized by $p_\Omega = (m\Omega^3/2\pi\alpha)$ (where $\alpha = e^2/\hbar c \simeq 1/137$ and c is the speed of light),

$$f(\Omega/\Omega_c) = \frac{(\Omega/\Omega_c)[1 + (\Omega/\Omega_c)^2]}{[1 - (\Omega/\Omega_c)^2]^2 + (\Gamma/\Omega_c)^2(\Omega/\Omega_c)^2},$$

and $\Pi(\theta) = \sqrt{2/[1 + (\Omega_c/\Omega)^2]}|e_x \cos\theta + e_y \sin\theta - i(\Omega_c/\Omega)^2(e_y \cos\theta - e_x \sin\theta)|$. In deriving Eq. (6), it is assumed that many LL's are occupied, so only the terms corresponding to the transitions between upper LL's are important, and, therefore, the matrix elements in the quasi-classical limit can be used.

Formulas (4) - (6) describe the dissipative and Hall microwave photoconductivities as functions of the normalized power of microwave radiation, its frequency and polarization, as well as the cyclotron frequency. In particular, these formulas yield oscillatory dependences of $\Delta\sigma_D$ and $\Delta\sigma_H$ on Ω/Ω_c and a nonlinear dependence of the amplitude on P . At $\Omega/\Omega_c \gtrsim \Lambda$, the microwave dissipative photoconductivity $\Delta\sigma_D < 0$. In this case, the net dissipative conductivity can be also negative if the microwave power is sufficiently large. In the vicinity of the cyclotron resonance ($\Omega \sim \Omega_c$) at moderate microwave powers $P \lesssim \min f^{-1} \sim (\Gamma/\Omega_c)^2$, one can take into account that $J_1^2(Lq\sqrt{P}f\Pi) \sim q^2 P f \Pi^2$ and obtain

$$C(P, \theta, \Omega, \Omega_c) \propto P \Pi^2(\theta) \frac{\Gamma f(\Omega/\Omega_c)(\Omega_c - \Omega)}{[(\Omega_c - \Omega)^2 + \Gamma^2]^2} S_i, \quad (7)$$

where $S_i = \mathcal{N}_i \int_0^\infty dq q^4 |V_q|^2 \exp(-L^2 q^2/2)$. Using Eqs. (4), (5), and (7), we arrive at

$$\Delta\sigma_D \simeq P \bar{\Delta}\sigma \Phi_D, \quad \Delta\sigma_H \simeq P \bar{\Delta}\sigma \Phi_H, \quad (8)$$

with

$$\bar{\Delta}\sigma \propto (1 - e^{-\hbar\Omega/T}) \frac{\Gamma f(\Omega/\Omega_c)(\Omega_c - \Omega)}{[(\Omega_c - \Omega)^2 + \Gamma^2]^2} S_i, \quad (9)$$

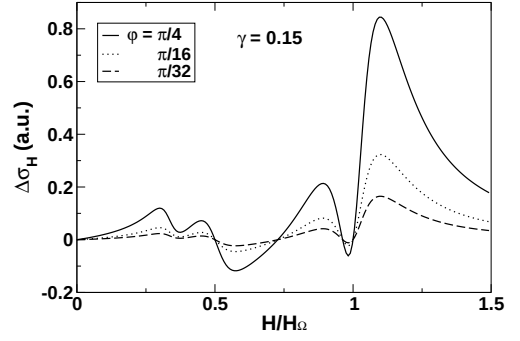


FIG. 1: Magnetic field dependencies of the Hall photoconductivity at different polarization angles.

$$\Phi_D = \frac{1}{2\pi} \int_0^{2\pi} d\theta \sin^2\theta \Pi^2(\theta), \quad (10)$$

$$\Phi_H = \frac{1}{2\pi} \int_0^{2\pi} d\theta \cos\theta \sin\theta \Pi^2(\theta). \quad (11)$$

In the case of circular polarization, $\Pi(\varphi) = 1$ at any ratio Ω/Ω_c and, hence, $\Phi_D = 1/2$ and $\Phi_H = 0$. At a linear polarization of the ac microwave field, introducing the angle between the directions of the dc and ac fields φ so that $e_x = \cos\varphi$ and $e_y = \sin\varphi$, we obtain

$$\Phi_D = \frac{1}{4} + \frac{\Omega^2 + (\Omega_c^2 - \Omega^2) \sin^2\varphi}{2(\Omega_c^2 + \Omega^2)}, \quad (12)$$

$$\Phi_H = \frac{1}{4} \left(\frac{\Omega_c^2 - \Omega^2}{\Omega_c^2 + \Omega^2} \right) \sin 2\varphi. \quad (13)$$

In the vicinity of the cyclotron resonance, Eqs. (10) and (11) yield $\Phi_D \simeq 3/4$ and $\Phi_H \simeq (\Omega_c^2 - \Omega^2) \sin 2\varphi / 8\Omega_c^2$. The obtained polarization dependences are consistent with the general symmetry properties of the photoconductivity tensor [36] as well as with the previous calculations [3, 4, 6, 37]. In particular, as follows from Eqs. (8) and (12), $\Delta\sigma_D$ exhibits larger amplitude of oscillations at $\varphi = \pi/2$ than at $\varphi = 0$ in agreement with the results of Ref. [6]. Equations (8), (12), and (13) show that the ratio of $\Delta\sigma_H$ and $\Delta\sigma_D$ at their maxima and minima corresponding to a cyclotron resonance harmonic is larger than this ratio at the maximum and minimum in the vicinity of the cyclotron resonance, where $\Phi_H \sim (\Gamma/\Omega_c) \sin 2\varphi$.

The conductivity tensor components are related to $\Delta\sigma_D$ and $\Delta\sigma_H$ as $\sigma_{xx} = \sigma_{yy} = \sigma_D + \Delta\sigma_D$, $\Delta\sigma_{xy} = \sigma_H + \Delta\sigma_H$, and $\Delta\sigma_{yx} = -\sigma_H + \Delta\sigma_H$, where σ_D and σ_H are the the dissipative and Hall conductivities without microwave radiation. As follows from the above results, both $\Delta\sigma_D$ and $\Delta\sigma_H$ do not vary when the magnetic field is reversed. This implies that in the situation under consideration, σ_{xy} and $-\sigma_{yx}$ are not equal to each other.

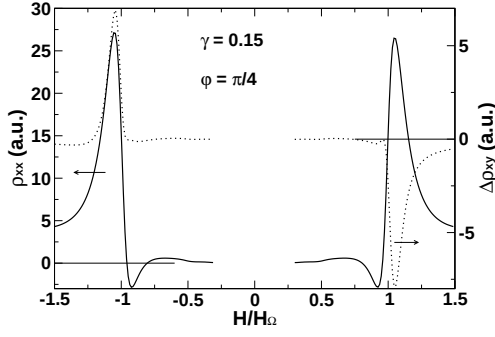


FIG. 2: Magnetic field dependencies of the dissipative (solid curves) and Hall (dotted curves) resistivities at $\varphi = \pi/4$.

Expressing the components of the conductivity tensor via σ_D , σ_H , $\Delta\sigma_D$, and $\Delta\sigma_H$, taking into account that $\sigma_H \gg \sigma_D, \Delta\sigma_D, \Delta\sigma_H$, and using Eq. (8), the variation of the Hall resistivity under the influence of microwave radiation can be presented in the following form:

$$\begin{aligned} \Delta\rho_{xy} &\simeq -\frac{\Delta\sigma_H}{\sigma_H^2} - \frac{(2\sigma_D + \Delta\sigma_D)\Delta\sigma_D}{\sigma_H^3} \\ &\simeq -P\frac{\overline{\Delta\sigma}}{\sigma_H^2} \left[\Phi_H + \frac{(2\sigma_D + P\overline{\Delta\sigma}\Phi_D)\Phi_D}{\sigma_H} \right]. \end{aligned} \quad (14)$$

Equation (14) qualitatively describes the following effects: (a) a shift of the ρ_{xy} vs H dependence (presence of a component which is an odd function of the magnetic field) stimulated by microwave radiation, (b) antisymmetric oscillations of $\Delta\rho_{xy}$ with varying magnetic field, and (c) markedly different span of $\Delta\rho_{xy}$ at $H \gtrsim H_\Omega$ and $H \lesssim H_\Omega$, i.e., at $\overline{\Delta\sigma} > 0$ and $\overline{\Delta\sigma} < 0$ [18, 19]. As follows from Eq. (14), $\Delta\rho_{xy}$ comprises a component (corresponding to the term proportional to $\Delta\sigma_H \propto P\Phi_H$) which is an even function of the magnetic field. According to Eqs. (13) and (14), this component essentially depends

on the polarization of microwave radiation. The term in Eq. (14) dependent on $\Delta\sigma_D \propto P\Phi_D$ changes its sign when the magnetic field reverses. Figure 1 shows the dependence of the Hall microwave photoconductivity $\Delta\sigma_H$ on the magnetic field normalized by $H_\Omega = mc\Omega/e$ calculated using the above equations. Figure 2 shows the magnetic field dependences of the dissipative and Hall resistivities in the vicinity of the cyclotron resonance calculated using general relationships between the components of the conductivity and resistivity tensors. It is assumed that the microwave power slightly exceeds the threshold of ANC. One can see that the $\Delta\rho_{xy}$ vs H dependence, in contrast to the magnetic field dependence of ρ_{xx} , exhibits an antisymmetrical behavior in reasonable agreement with the experimental results [18, 19] (compare with Fig. 2(b) from Ref. [18] and Fig. 1(c) from Ref. [19]). As seen from Fig. 2, the calculated dissipative resistivity ρ_{xx} is negative when $|H| \lesssim H_\Omega$. In this range of magnetic fields, uniform states of a 2DES can be unstable resulting in the formation of complex domain structures with the net resistance close to zero. In these calculations we put $\sigma_H/\sigma_D = 100$ at $H = 1.5$ kG and $\gamma = \Gamma/\Omega = 0.15$. By convention the plots shown in Figs. 1 and 2 can be attributed to a AlGaAs/GaAs 2DES with the electron mobility $\mu = 1.5 \times 10^7$ cm²/Vs irradiated with microwaves with the frequency $\Omega/2\pi = 50$ GHz. The dependence of ρ_{xx} and $\Delta\rho_{xy}$ on the microwave power becomes nonlinear at its elevated values. This also leads to an alteration of the polarization dependences. However, this problem needs a separate study.

In summary, we calculated the dependences of the dissipative and Hall resistivities in 2DES under microwave radiation on the magnetic field (its strength and sign) and the radiation polarization. We showed that microwave irradiation can lead to variations of the Hall resistivity which are even and odd oscillatory functions of the magnetic field. The obtained dependences are consistent with recent experimental data [18, 19].

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